



Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	34	$^{\circ}C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	180	$^{\circ}C/W$
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	$^{\circ}C$

Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2		-2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-60V, V_{GS}=0V$			-1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance	0	$V_{GS}=-10V, I_D=-8.5A$				
		$V_{GS}=-4.5V, I_D=-6A$				
Forward Transconductance	g_{FS}	$V_{DS}=-10V, I_D=-4A$				
Diode Forward Voltage	V_{FSD}	$I_S=-8.5A$				

Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz$ $V_{DS}=25V$	-	3500	-	pF
Output capacitance	C_{oss}		-	330	-	
Reverse transfer capacitance	C_{rss}		-	96	-	

Gate Charge characteristics($T_a = 25$)

Parameter	Symbol	Condition	Min.	Typ	Max.
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Fig.13 Switching Time Measurement Circuit

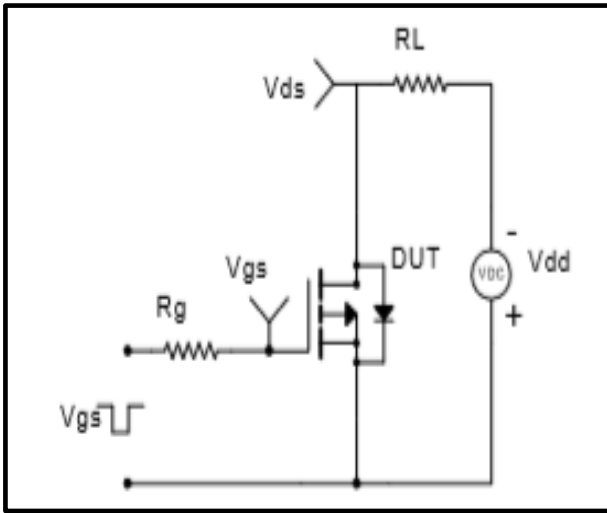
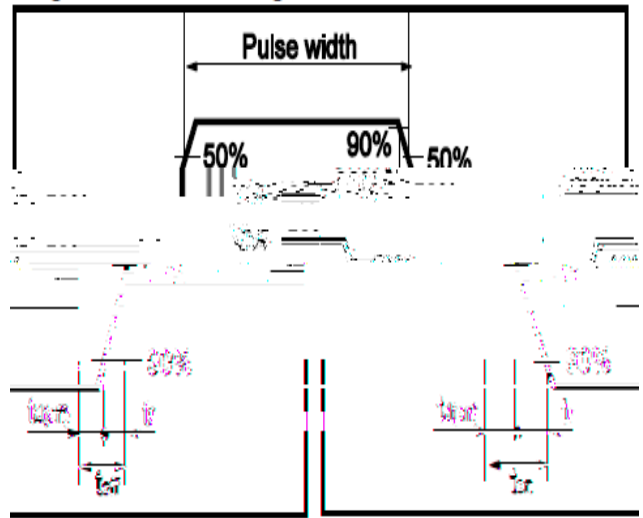


Fig.14 Gate Charge Waveform





Dimensions(SOP8)

Unit: mm

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.25	C	1.30		1.75
A1	0.37		0.49	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20